

# Switching Diode BAS16L

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V <sub>R</sub>	100	V
Peak Forward Current	ΙF	200	mA
Non-Repetitive Peak Forward Surge Current 60 Hz	I <sub>FSM(surge)</sub>	1.8	Α
Repetitive Peak Forward Current (Note 3)	I <sub>FRM</sub>	1.0	Α
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^{\circ}C$ prior to surge) $t = 1 \ \mu s$ $t = 10 \ \mu s$ $t = 100 \ \mu s$ $t = 1 \ ms$ $t = 10 \ ms$ $t = 100 \ ms$ $t = 10 \ ms$	IFSM	36.0 18.0 6.0 3.0 1.8 1.3	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

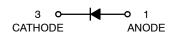
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1

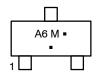
- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
- 3. Square Wave, f = 40 kHz, PW = 200 ns Test Duration = 60 s, T<sub>J</sub> =  $25^{\circ}\text{C}$  prior to surge.



STYLE 8



#### **MARKING DIAGRAM**



A6 = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

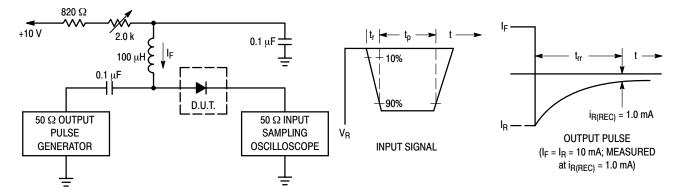
Device	Package	Shipping <sup>†</sup>
BAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel
SBAS16LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
SBAS16LT3G	SOT-23 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•			
Reverse Voltage Leakage Current $(V_R = 100 \text{ V})$ $(V_R = 75 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I <sub>R</sub>	- - -	1.0 50 30	μAdc
Reverse Breakdown Voltage (I <sub>BR</sub> = 100 μAdc)	V <sub>(BR)</sub>	100	-	Vdc
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V <sub>F</sub>	- - - -	715 855 1000 1250	mV
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	C <sub>D</sub>	-	2.0	pF
Forward Recovery Voltage (I <sub>F</sub> = 10 mAdc, t <sub>r</sub> = 20 ns)	V <sub>FR</sub>	-	1.75	Vdc
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega)$	t <sub>rr</sub>	-	6.0	ns
Stored Charge (I <sub>F</sub> = 10 mAdc to V <sub>R</sub> = 5.0 Vdc, R <sub>L</sub> = 500 $\Omega$ )	Q <sub>S</sub>	-	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

## BAS16L

# **TYPICAL CHARACTERISTICS**

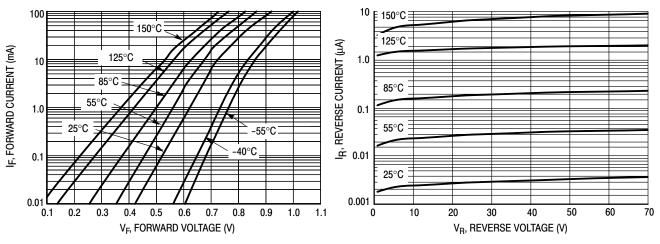


Figure 2. V<sub>F</sub> vs. I<sub>F</sub>

Figure 3. I<sub>R</sub> vs. V<sub>R</sub>

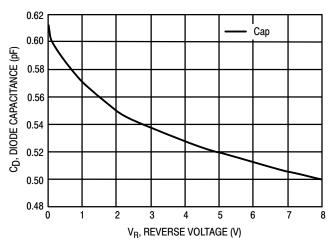


Figure 4. Capacitance

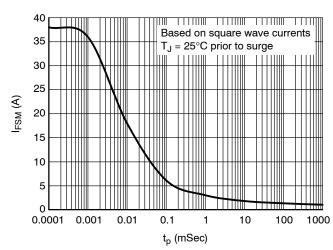


Figure 5. Maximum Non-repetitive Peak Forward Current as a Function of Pulse Duration, Typical Values

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

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### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

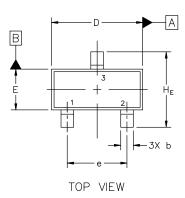
2.04

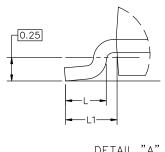
0.55

0.69

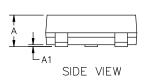
2.64

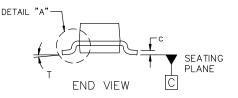
10°

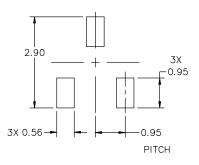




DETAIL "A" Scale 3:1







#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

# **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

## RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

# SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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